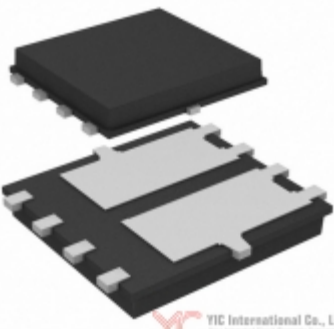

	<h2 style="color: #E67E22;">SI7900AEDN-T1-E3</h2>
	Hersteller-Teilenummer: SI7900AEDN-T1-E3
	Hersteller / Marke: Vishay / Siliconix
	Teil der Beschreibung: MOSFET 2N-CH 20V 6A 1212-8
	Datenblätter:  SI7900AEDN-T1-E3.pdf
	RoHs Status: Bleifrei / RoHS-konform
	Lagerzustand: New original, 107182 pcs Stock Available.
Liefern von: Hong Kong	
Versandweg: DHL/Fedex/TNT/UPS/EMS	
<p>Image may be representation. See specs for product details.</p>	

Spezifikationen

Teilenummer	SI7900AEDN-T1-E3
Hersteller	Vishay / Siliconix
Beschreibung	MOSFET 2N-CH 20V 6A 1212-8
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs,
Teilstatus	107182 pcs Stock
Serie	TrenchFET®
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Leistung - max	1.5W
Verpackung / Gehäuse	PowerPAK® 1212-8 Dual
Supplier Device-Gehäuse	PowerPAK® 1212-8 Dual
Typ FET	2 N-Channel (Dual) Common Drain
FET-Merkmal	Logic Level Gate
Drain-Source-Spannung (Vdss)	20V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	6A
Rds On (Max) @ Id, Vgs	26 mOhm @ 8.5A, 4.5V
VGS (th) (Max) @ Id	900mV @ 250µA
Gate Charge (Qg) (Max) @ Vgs	16nC @ 4.5V
Eingabekapazität (Ciss) (Max) @ Vds	-
Verpackung	Tape & Reel (TR)

SI7900AEDN-T1-E3 ist neu im Original, Suche SI7900AEDN-T1-E3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI7900AEDN-T1-E3 Vishay / Siliconix mit Garantie und Vertrauen. Anfrage SI7900AEDN-T1-E3: Info@Y-IC.com

Sie können auch interessiert sein:

 SI7900AEDN-T1 VISHAY SI7900AEDN-T1 VISHAY	 SI7900AEDN-T1-E3 Electro-Films (EFI) / Vishay MOSFET 2N-CH 20V 6A 1212-8	 SI7900EDIV-T1-E3 VISHAY VISHAY QFN	 SI7898DP-T1-GE3 Electro-Films (EFI) / Vishay MOSFET N-CH 150V 3A PPAK SO-8
 SI7900DN VISHAY VISHAY QFN-8	 SI7900AEDN-T1-GE3 Electro-Films (EFI) / Vishay MOSFET 2N-CH 20V 6A PPAK 1212-8	 SI7900AEDN-T1-GE3 Vishay / Siliconix MOSFET 2N-CH 20V 6A PPAK 1212-8	 SI7900AEDN SI SI7900AEDN SI

heiße Teile

Mehr

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|---|---|---|--|--|
|  SI7886DP-T1-GE3 |  SI7888DP-T1-E3 |  SI7888DP-T1-E3 |  SI7888DP-T1-GE3 |  SI7888DP-T1-GE3 |
|  SI7892ADP-T1-E3 |  SI7892ADP-T1-GE3 |  SI7892ADP-T1-GE3. |  SI7892BDP-T1-E3 |  SI7892BDP-T1-E3 |
|  SI7892BDP-T1-GE3 |  SI7892BDP-T1-GE3 |  SI7892DP |  SI7892DP-T1 |  SI7892DP-T1-E3 |
|  SI7892DP-T1-GE3 |  SI7898DP |  SI7898DP-T1-E3 |  SI7898DP-T1-E3 |  SI7898DP-T1-GE3 |
|  SI7898DP-T1-GE3 |  SI7900ADN |  SI7900AEDN |  SI7900AEDN-T1 |  SI7900AEDN-T1-E3 |
|  SI7900AEDN-T1-GE3 |  SI7900AEDN-T1-GE3 |  SI7900EDN |  SI7900EDN-T1 |  SI7900EDN-T1-E3 |
|  SI7900EDN-T1-GE3 |  SI7901EDN-T1 |  SI7901EDN-T1-E3 |  SI7901EDN-T1-E3 |  SI7904BDN-T1-E3 |
|  SI7904BDN-T1-E3 |  SI7904BDN-T1-GE3 |  SI7904BDN-T1-GE3 |  SI7904DN |  SI7904DN-T1 |
|  SI7904DN-T1-E3 |  SI7904DN-T1-E3 |  SI7904DN-T1-GE3 |  SI7904DN-T1-GE3 |  SI7905DN-T1-GE3 |
|  SI7905DN-T1-GE3 |  SI7909DN-T1-E3 |  SI7909DN-T1-E3 |  SI7909DN-T1-GE3 |  SI7909DN-T1-GE3 |

Contact us: Info@Y-IC.com

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